

Title (en)
SEMICONDUCTOR STRUCTURE WITH ONE OR MORE LATERAL HIGHLY BLOCKING SEMICONDUCTOR COMPONENTS

Title (de)
HALBLEITERSTRUKTUR MIT EINEM ODER MEHREREN LATERALEN, HOCH SPERRENDEN HALBLEITERBAUELEMENTEN

Title (fr)
STRUCTURE A SEMI-CONDUCTEURS COMPORTANT UN OU PLUSIEURS COMPOSANTS SEMI-CONDUCTEURS LATéraux BLOQUANT HAUT

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Application
EP 93901752 A 19921223

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Abstract (en)
[origin: DE4201276C1] The object of the invention is a semiconductor structure with one or more lateral highly blocking semiconductor components in a semiconductor consisting of a metallised substrate (2), a dielectric layer (3) adjoining the substrate, a uniformly doped drift region (4) above the dielectric layer and heavily doped regions of the semiconductor components which are embedded in the drift region and electrically bonded. At least the regions (5, 6) of the semiconductor components, which can, during relevant operation of said components, exhibit a high potential difference with respect to the substrate, extend as far as the dielectric layer (3).

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